

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BM100-28** is Designed for high power VHF Applications up to 200 MHz.

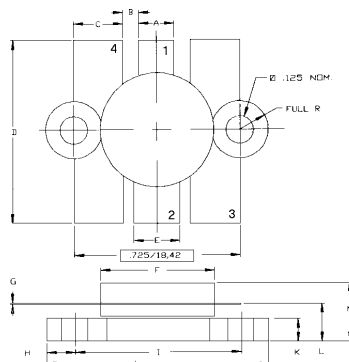
FEATURES:

- Common Emitter
- $P_G = 8.5 \text{ dB}$ at 20 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CEO}	33 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.65°C/W

PACKAGE STYLE .500 6L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06
B	.045/1.14	
C	.210/5.33	.220/5.59
D	.835/21.21	.865/21.97
E	.200/5.08	.210/5.33
F	.490/12.45	.510/12.95
G	.003/0.08	.007/0.18
H	.125/3.18	
I	.720/18.29	.730/18.54
J	.970/24.64	.980/24.89
K	.095/2.41	.105/2.67
L	.150/3.81	.170/4.32
M	.280/7.11	

1 = COLLECTOR 2 = BASE 3&4 = EMITTER

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50 \text{ mA}$		33			V
BV_{CES}	$I_C = 100 \text{ mA}$		65			V
BV_{EBO}	$I_E = 5.0 \text{ mA}$		4.0			V
h_{FE}	$V_{CE} = 5.0 \text{ V}$	$I_C = 1.0 \text{ A}$	10			---
C_{CB}	$V_{VB} = 28 \text{ V}$	$f = 1.0 \text{ MHz}$		200		pF
P_G η_C	$V_{CC} = 28 \text{ V}$	$P_{OUT} = 100 \text{ W}$ $f = 175 \text{ MHz}$	8.5	60		dB %